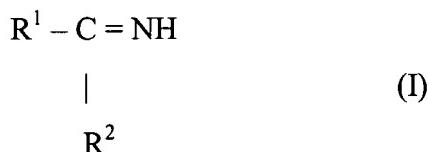


In the Claims:

1. (Currently amended) A solution useful for removing a barrier material from a semiconductor substrate comprising by weight percent 0.01 to 25 oxidizer, 0 to 15 inhibitor for a nonferrous metal, 0 to 15 abrasive, 0 to 20 complexing agent for the nonferrous metal, 0.01 to 12 barrier removal agent selected from imine derivative compounds

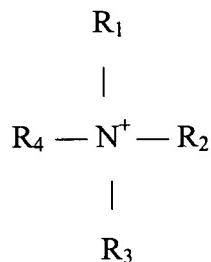


where the imine derivative compound is selected from formamidine, formamidine salts, formamidine derivatives, guanidine derivatives, guanidine salts and mixtures thereof, with the formamidine derivative being formamidinesulfinic acid, and the guanidine derivative being selected from the list of 1,3-diphenyl guanidine, 1-methyl-3-nitroguanidine, guanidine hydrochloride, amino-guanidine hydrochloride, tetramethylguanidine, and 2,2-azobis (dimethyl-propionamidine)di-HCl, guanidine sulfate, guanidine acetic acid, guanidine carbonate and guanidine nitrate or mixtures thereof, hydrazine derivative compounds



where R^3 , R^4 , R^5 , and R^6 are independently $-\text{H}$, $-\text{OR}^7$ where R^7 is a hydrocarbon group, $-\text{NH}_2$, a hydrocarbon group, a carbonyl group, an imido group, an azo group, a cyano group, a thio group, or a seleno group,

and mixtures thereof, 0.01 to 10 organic-containing ammonium salt formed with



R₁, R₂, R₃ and R₄ are radicals, R₁, R₂, R₃ and R₄ is-aare substituted or unsubstituted aryl, alkyl, aralkyl, or alkaryl group and has-have a carbon chain length of 2 to 10 carbon atoms and balance water; and the solution has a pH less than 7 and a tantalum nitride to CDO selectivity of at least 2 to 1 as measured with a microporous polyurethane polishing pad with at least one pressure measured normal to a wafer of equal to or less than 13.8 kPa.

2. (Previously presented) The solution of claim 1 wherein the barrier removal agent is imine derivative compound and the imine derivative compound is present in an amount of 0.1 to 10 weight percent.

3. (Currently amended) The solution of claim 1 wherein the oxidizer is selected from hydrogen peroxide, monopersulfates, iodates, magnesium perphthalate, peracetic acid, persulfates, bromates, perbromates, perchlorates, periodates, ferric nitrate, iron salts, cerium salts, Mn (III) salts, Mn(IV) salts and Mn (VI) salts, silver salts, copper salts, chromium salts, cobalt salts, halogens, hypochlorites and-or mixtures thereof.

4. (Currently amended) The solution of claim 1 wherein the solution includes the hydrazine derivative compound and imine derivative compound is selected from amino-guanidine hydrochloride, formamidine, formamidinesulfinic acid, formamidine acetate, 1,3-diphenyl guanidine, 1-methyl-3-nitroguanidine, guanidine hydrochloride, tetramethylguanidine, 2,2-azobis (dimethyl propionamidine)di HCl, guanidine sulfate, guanidine acetic acid, guanidine carbonate, guanidine nitrate and mixtures thereof and the hydrazine derivative compound is selected from carbohydrazide, acetic hydrazide, semicarbazide hydrochloride, 1,2-diformylhydrazine, methylhydrazino-carboxylate, oxalic dihydrazide, acetone azine and formic hydrazide and mixtures thereof.

5 to 10 Cancelled.

11. (Previously presented) The solution of claim 1 wherein the solution is abrasive-free.

12 to 19 Cancelled.